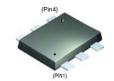


April 2010

## 2N7002V/VA N-Channel Enhancement Mode Field Effect Transistor

### **Features**

- Dual N-Channel MOSFET
- · Low On-Resistance
- · Low Gate Threshold Voltage
- Low Input Capacitance
- · Fast Switching Speed
- · Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- · Lead Free By Design/RoHS Compliant



**SOT-563F**\* Pin1 and Pin4 are exchangeable.



2N7002V Marking : AB



2N7002VA Marking : AC

### **Absolute Maximum Ratings \*** T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter		Value	Units
V <sub>DSS</sub>	Drain-Source Voltage		60	V
$V_{DGR}$	Drain-Gate Voltage $R_{GS} \le 1.0 M\Omega$		60	V
V <sub>GSS</sub>	Gate-Source Voltage	Continuous Pulsed	±20 ±40	V
I <sub>D</sub>	Drain Current	Continuous Pulsed	280 1.5	mA A
T <sub>J</sub> , T <sub>STG</sub>	Junction and Storage Temperature Range		-55 to +150	°C

<sup>\*</sup> These ratings are limiting values above which the serviceability of any semiconductor device may by impaired.

### **Thermal Characteristics**

Symbol	Parameter	Value	Units	
P <sub>D</sub>	Total Device Dissipation Derating above T <sub>A</sub> = 25°C	250 2.0	mW mW/°C	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient *	500	°C/W	

<sup>\*</sup> Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch, Minimum land pad size.

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# **Electrical Characteristics** $T_A = 25$ °C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
Off Charac	cteristics (Note1)			•	•	•
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS}=0V$ , $I_D=10\mu A$	60	78	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V V <sub>DS</sub> =60V, V <sub>GS</sub> =0V, @T <sub>C</sub> =125°C	-	0.001 7	1.0 500	μА
I <sub>GSS</sub>	Gate-Body Leakage	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	0.2	±100	nA
On Charac	cteristics (Note1)					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	1.0	1.76	2.5	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =5V, I <sub>D</sub> =0.05A, V <sub>GS</sub> =10V, I <sub>D</sub> =0.5A, @T <sub>J</sub> =125°C	-	1.6 2.53	7.5 13.5	Ω
I <sub>D(ON)</sub>	On-State Drain Current	V <sub>GS</sub> =10V, V <sub>DS</sub> =7.5V	0.5	1.43	-	Α
9FS	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =0.2A	80	356.5	-	mS
Dynamic	Characteristics				•	
C <sub>iss</sub>	Input Capacitance		-	37.8	50	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0MHz	-	12.4	25	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		-	6.5	7.0	pF
Switching	Characteristics	•				•
t <sub>D(ON)</sub>	Turn-On Delay Time	V <sub>DD</sub> =30V, I <sub>D</sub> =0.2A, V <sub>GEN</sub> =10V	-	5.85	20	nc
t <sub>D(OFF)</sub>	Turn-Off Delay Time	$R_L=150\Omega$ , $R_{GEN}=25\Omega$	-	12.5	20	ns

Note1: Short duration test pulse used to minimize self-heating effect.

## **Typical Performance Characteristics**

Figure 1. On-Region Characteristics

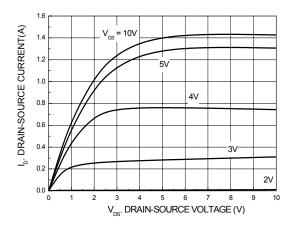


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current

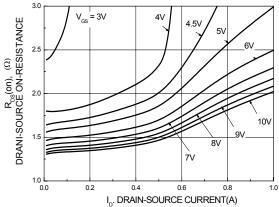


Figure 3. On-Resistance Variation with Temperature

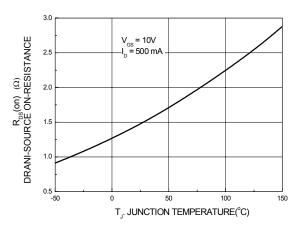


Figure 4. On-Resistance Variation with Gate-Source Voltage

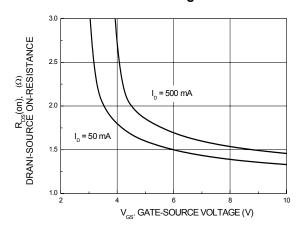


Figure 5. Transfer Characteristics

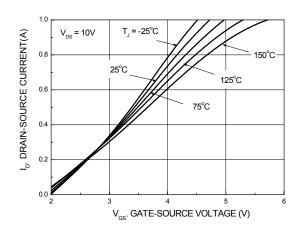
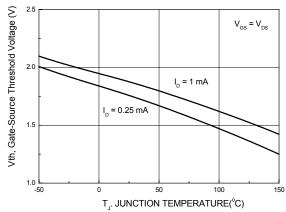


Figure 6. Gate Threshold Variation with Temperature



## **Typical Performance Characteristics**

Figure 7. Reverse Drain Current Variation with Diode Forward Voltage and Temperature

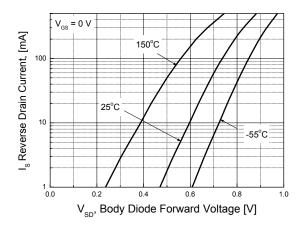
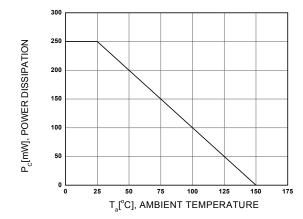
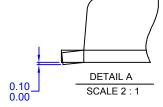


Figure 8. Power Derating



# **Package Dimensions SOT-563F** Α - 0.50 \_0.30 0.15 0.50 1.20 BSC 1.60 1.25 □ 0.1 C B A (0.20)0.30 0.50 1.00 **TOP VIEW** LAND PATTERN RECOMMENDATION \_0.18 \_0.10 SEE DETAIL A C 0.35 BSC 0.20 BSC



Dimensions in Millimeters

**BOTTOM VIEW** 



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No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
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